LN	lumber	Hits	S   Search Text	1.55	
1	- unibci	60765		DB	Time stamp
		00,00	(cit (chin ad) film adj (fansistor))	USPAT;	2004/05/14 10:54
				US-PGPUB;	·
	,			EPO; JPO; DERWENT	
2 .		22061	((tft (thin adj film adj transistor))) and	USPAT:	2004/05/14 10:54
		İ	gate and drain and source	US-PGPUB;	2004/05/14 10:54
				EPO; JPO;	
				DERWENT	
. 3		18869		USPAT;	2004/05/14 10:55
1			and gate and drain and source) and	US-PGPUB;	2004/03/14 10:55
	i	,	substrate	EPO; JPO;	
1		4 7 6 6 6		DERWENT	
4		17602		USPAT;	2004/05/14 10:55
			and gate and drain and source) and	US-PGPUB;	
			substrate) and electrode	EPO; JPO;	
5		15033	////+f+ /+him odi 5:1	DERWENT	
1.		13033	<pre>(((((tft (thin adj film adj transistor))) and gate and drain and source) and</pre>	USPAT;	2004/05/14 10:56
			substrate) and electrode) and (method	US-PGPUB;	
			process)	EPO; JPO;	·
6		13007		DERWENT	0004/05/11
1 .			and gate and drain and source) and	USPAT; US-PGPUB;	2004/05/14 10:56
	•		substrate) and electrode) and (method	EPO; JPO;	
			process)) and (gate adj electrode)	DERWENT	47 7 7 7 7 7 7 7
7		3555	((((((tft (thin adj film adj	USPAT;	2004/05/14 10:56
-			transistor))) and gate and drain and	US-PGPUB;	2004/03/14 10.56
,		4.	source) and substrate) and electrode) and	EPO; JPO;	
			(method process)) and (gate adj	DERWENT	
8		0141	electrode)) and (gate adj line)		
l°		2141	(((((((tft (thin adj film adj	USPAT;	2004/05/14 10:57
			transistor))) and gate and drain and	US-PGPUB;	
	٠.		source) and substrate) and electrode) and (method process)) and (gate adj	EPO; JPO;	
	.		electrode)) and (gate adj line)) and mask	DERWENT	
ġ		958	((((((((tft (thin adj film adj	110000	
			transistor))) and gate and drain and	USPAT;	2004/05/14 10:57
			source) and substrate) and electrode) and	US-PGPUB; EPO; JPO;	1
			(method process)) and (gate adj	DERWENT	
	·	, ,	electrode)) and (gate adj line)) and mask)	DEKWENT	
	1		and reflect\$3		
10		2141	((((((((tft (thin adj film adj	USPAT;	2004/05/14 10:58
	1		transistor))) and gate and drain and	US-PGPUB;	
	ŀ		source) and substrate) and electrode) and	EPO; JPO;	
			(method process)) and (gate adj	DERWENT	
ļ	ĺ		electrode)) and (gate adj line)) and mask)		
11		80	<pre>and (reflect\$3 (line layer)) (((((((tft (thin adj film adj</pre>		
	. , '		transistor))) and gate and drain and	USPAT;	2004/05/14 10:58
	. 1		source) and substrate) and electrode) and	US-PGPUB; EPO; JPO;	
	- 1	*	(method process)) and (gate adj	DERWENT	
	- <i>i</i> -		electrode)) and (gate adj line)) and mask)	→ F1744 F14 T	
	1		and (reflect\$3 adj (line laver))		
12		15	(((((((((tft (thin adj film adj	USPAT;	2004/05/14 10:59
			transistor))) and gate and drain and	US-PGPUB;	=001,00,11 10.55
			source) and substrate) and electrode) and	EPO; JPO;	
			(method process)) and (gate adj	DERWENT	
		- 1	electrode)) and (gate adj line)) and mask)		
	1		and (reflect\$3 adj (line layer))) and		
13		41	<pre>(ohmic near1 (contact layer)) (((((((((tft (thin adj film adj</pre>		
		3.4	transistor))) and gate and drain and	USPAT;	2004/05/14 10:59
	- [		source) and substrate) and electrode) and	US-PGPUB;	
			(method process)) and (gate adj	EPO; JPO;	
			electrode)) and (gate adi line)) and mask)	DERWENT	
			and (reflect\$3 adj (line laver))) and		
			transmissive		

14	12	<pre>((((((((((((((((((((((((((((((((((((</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 10:59
15 16 17	1 0 3	6620655.URPN.	USPAT USPAT USPAT	2004/05/14 11:01 2004/05/14 11:01 2004/05/14 11:01